

Lecture 24: Slew Rate, Settling Time, & PSRR

• Announcements:

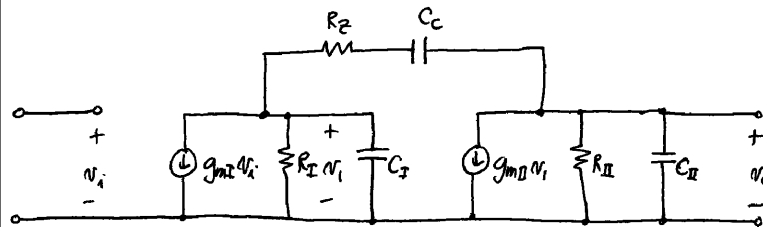
- Hutton online
- Design Project Checkpoint:
  - ↳ Due Monday, April 23, 11:59 p.m.
  - ↳ Send to your TA a spice file for your op amp design that simulates correctly, i.e., that reaches a stable bias point where all transistors are saturated (or linear if an MOS resistor)
  - ↳ It doesn't need to meet the project specs, but it should simulate correctly

• Lecture Topics:

- ↳ Nulling the RHP Zero (finish compensation)
- ↳ Slew Rate (revisited)
- ↳ Settling Time
- ↳ Power Supply Rejection Ratio (PSRR)

• Last Time:

Nulling Resistor in Series w/  $C_C$



Doing KCL: 
$$P_1 \approx -\frac{1}{g_{mII} R_I R_{II} C_C}$$

$$P_2 \approx \frac{-g_{mII} C_C}{C_I C_{II} + C_C (C_I + C_{II})}$$
 } same as before

$$P_3 = -\frac{1}{R_2 C_I} \leftarrow \text{pole due to } R_2$$

$$Z_1 = \frac{1}{C_C \left( \frac{1}{g_{mII}} - R_2 \right)} \leftarrow \text{relocated zero (function of } R_2 \text{)}$$

Zero Placement Strategies

① Eliminate  $Z_1 \rightarrow$  move it to  $\infty$ :

$$Z_1 = \frac{1}{C_C \left( \frac{1}{g_{mII}} - R_2 \right)} \rightarrow \infty \text{ when } R_2 = \frac{1}{g_{mII}}$$

After doing this: 
$$P_3 \approx -\frac{g_{mII}}{C_I} \left. \begin{array}{l} \text{usually, } \\ C_{II} \gg C_I \end{array} \right\}$$

$$P_2 \approx -\frac{g_{mII}}{C_{II}} \left. \begin{array}{l} \\ \text{since } C_{II} = C_L \end{array} \right\}$$

so these poles are often very far apart.  
 (but be careful)

This is good... but we could do better...

② Eliminate  $P_3$  by placing  $Z_1$  on top of it:

$$Z_1 \approx P_3 = \frac{1}{C_C \left( \frac{1}{g_{mII}} - R_2 \right)} = -\frac{1}{R_2 C_I}$$

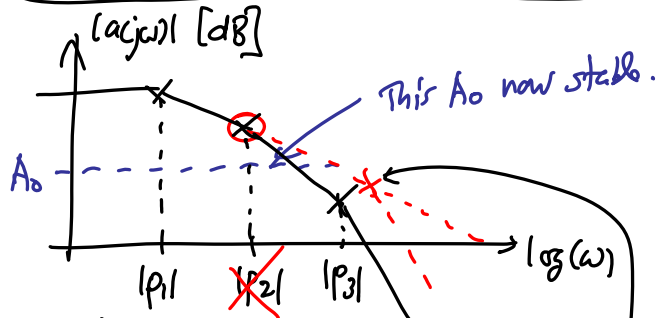
$$R_2 = \frac{1}{g_{mII} \left( 1 - \frac{C_I}{C_C} \right)}$$

After this:

- ①  $p_3$  gone;  $p_1$  &  $p_2$  left
- ② Now, can place  $\omega_{\text{unit}}$  @  $p_2$  and really get  $PM=45^\circ$  (w/o worrying about the influence of  $p_3$ )
- ③ Eliminate  $p_2$  by placing  $z_1$  on top of it:

$$z_1 = p_2 \Rightarrow \frac{1}{C_c \left( \frac{1}{g_{mI}} - R_2 \right)} = - \frac{g_{mII}}{C_{II}}$$

$$R_2 = \frac{(C_c + C_{II}) \left( \frac{1}{g_{mI}} \right)}{C_c} = \frac{1}{g_{mI}} \left( 1 + \frac{C_{II}}{C_c} \right)$$



With this choice of  $R_2$ :

$$p_3 = - \frac{1}{R_2 C_I} = - \frac{1}{\left( \frac{C_c + C_{II}}{C_c} \right) \left( \frac{1}{g_{mI}} \right) C_I}$$

$$p_3 = - \frac{g_{mI} C_c}{C_I (C_c + C_{II})}$$

← This is the new  $p_2$

For  $PM=45^\circ$ :

$$C_c = \frac{g_{mI}}{|p_3| A_0} = \frac{g_{mI}}{g_{mII}} \frac{C_I (C_c + C_{II})}{C_c A_0}$$

↪ solve for  $C_c$

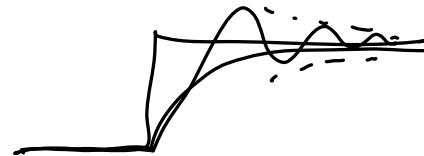
For  $PM=60^\circ$ :

$$C_c = \frac{1.73 g_{mI}}{|p_3| A_0} \xrightarrow{[C_I \ll C_{II}]} C_c \approx \sqrt{\frac{1.73 g_{mI} C_I C_{II}}{g_{mII} A_0}}$$

↪ For  $PM=60^\circ$

Remark. If settling time is important, then approach ③ may not be the best approach. The reason is that if the zero is not exactly equal to the pole, the a "doublet" ensues, which actually can hurt the settling time.

Discussed in a handout to be posted on the course website. → also, discussed in Razavi, problem 10.19.



**Actual Implementation**  
 ⇒ resistor are too big! → ∴ implement using a much smaller MOS resistor!

**MOS Resistor:** just an MOS transistor operated in the linear region

linear region  
 saturation  
 $I_d = \mu_n C_{ox} \frac{W}{L} [(V_{gs} - V_t)V_{ds} - \frac{1}{2}V_{ds}^2]$   
 $\frac{\partial I_d}{\partial V_{ds}} = \mu_n C_{ox} \frac{W}{L} (V_{gs} - V_t - V_{ds})$

linear R

$R_{s.s.} = \left[ \frac{dI_d}{dV_{ds}} \right]^{-1} \Big|_{V_{gs}=V_{gs}, V_{ds}=V_{ds}} = \frac{1}{\mu_n C_{ox} \frac{W}{L} (V_{gs} - V_t - V_{ds})} \approx \frac{1}{3I_{ds}}$

a variable resistor controlled by  $V_{gs}$ !

**Actual Implementation**

(to be continued in the next lecture)

**Slew Rate (f/better)**

Using Laplace Xform Theory:

$$\frac{V_o}{V_i}(s) = \frac{1}{1 + \frac{s}{\omega_c}} = \frac{1}{1 + s\tau_c} \quad \tau_c = \frac{1}{\omega_c}$$

single (dominant) pole

$$V_i(s) = \frac{V_A}{s}$$

$$V_o(s) = \frac{V_A}{s(1 + s\tau_c)} = \frac{V_A}{s} - \frac{V_A}{s + \frac{1}{\tau_c}}$$

↑ Inverse Laplace Xform → the constant

$$V_o(t) = V_A(1 - e^{-t/\tau_c}) \leftarrow \text{expected response}$$

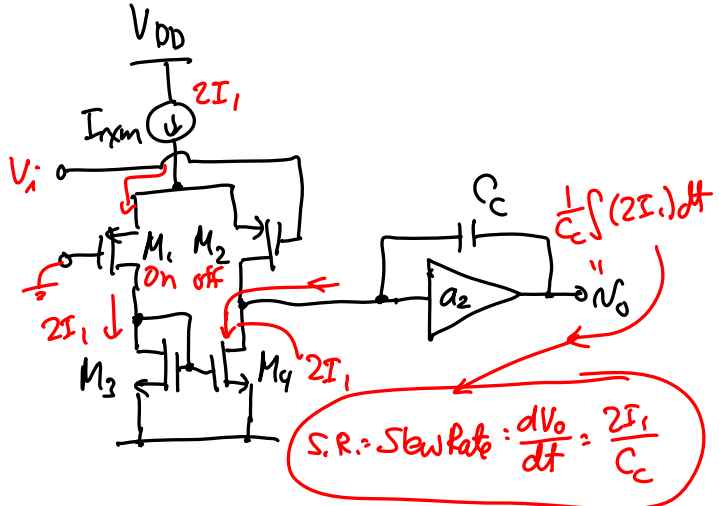
open loop op amp  
 closed loop unity gain buffer

**Theoretical Expectation**

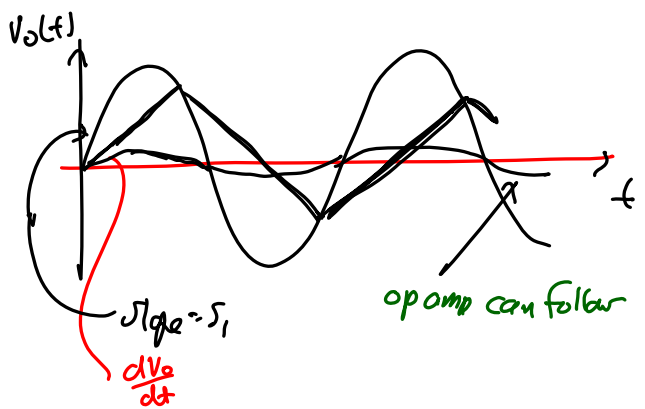
**Reality Why?**

—  $\frac{dV_o}{dt}$  ←

Reasons 1<sup>st</sup> or 2<sup>nd</sup> stage of op amp cannot source enough current to mimic the slope (or speed) of a fast rising input signal



Ex. If apply a very fast (i.e., high freq., large amplitude) sinusoid:



In terms of design variables:

$$S.R. = \frac{dV_o}{dt} = \frac{I_{xm}}{C_c} = \left[ \frac{I_{xm}}{G_{m1}} \omega_{ult} A_o = S.R. \right]$$

$$C_c = \frac{G_{m1}}{\omega_{ult} A_o} \leftarrow \text{closed-loop gain}$$

$\omega_{ult} = \omega @ |a(j\omega)f| = 1$

To Increase S.R.:

- ① Decrease  $G_{m1}$  ← transconductance of 1<sup>st</sup> stage
- ② Increase  $\omega_{ult}$  → increase  $\omega_2$   
 ↓ limited by the Xstart freq. range
- ③ Use a larger  $A_o$ , if possible.  
 closed loop gain ↑ (only if permitted by the application)

Increasing S.R. via  $G_m$ -Reduction

① Emitter or Source Degeneration of the Input Stage -

$SR = \frac{2I_1}{G_{m1}} \omega_{ult} A_0$  ←  $I_1$  remains the same

$G_{m1} = \frac{g_{m1}}{1 + g_{m1} R_E}$  ↓ → SR ↑

Limitations:

- ①  $R_E$  mismatch →  $V_{os}$   
 ↓ must limit  $V_{RE}$  to limit  $V_{os}$
- ②  $R_E$  ↑ → gain ↓ (SR-gain trade-off)
- ③  $R_E$  contributes thermal noise → must limit to preserve the noise performance of the op amp.

② FET Input Devices -

JFETs → can be made in bipolar technology  
 very large  $R_i$

For FET's:  $\frac{g_m}{I_D} \approx \frac{2}{V_{GS} - V_T}$  ← ~0.2V

For BJT's:  $\frac{g_m}{I_C} = \frac{1}{V_T}$  ← 26mV

FET S.R. =  $\frac{I_D}{g_{mF}} \omega_{ult} = \frac{V_{GS} - V_T}{2} = \frac{V_{GS} - V_T}{2V_T} = \frac{260}{26} \times 10$

BJT S.R. =  $\frac{I_C}{g_{mB}} \omega_{ult}$

Limitations:

- ① High  $V_{os}$ .
- ② Increased voltage noise.  
 (But decreased current noise.)

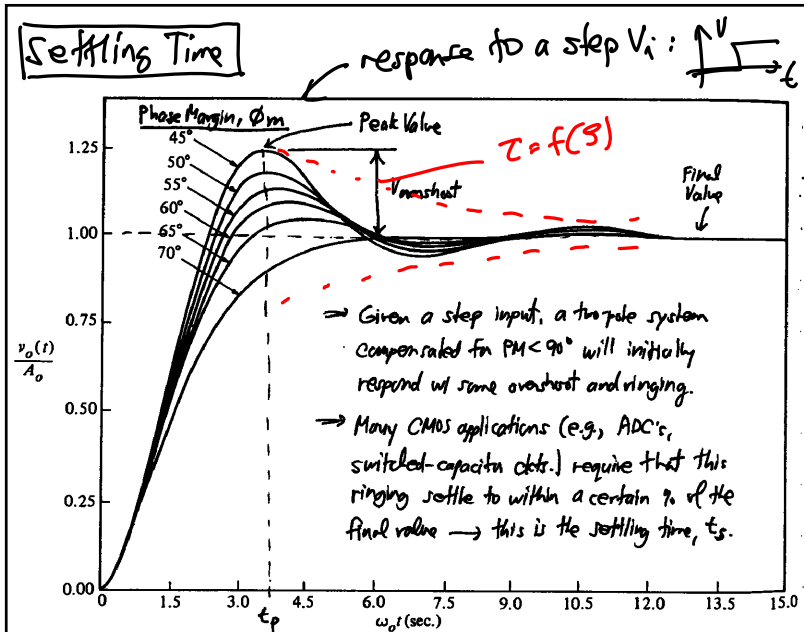
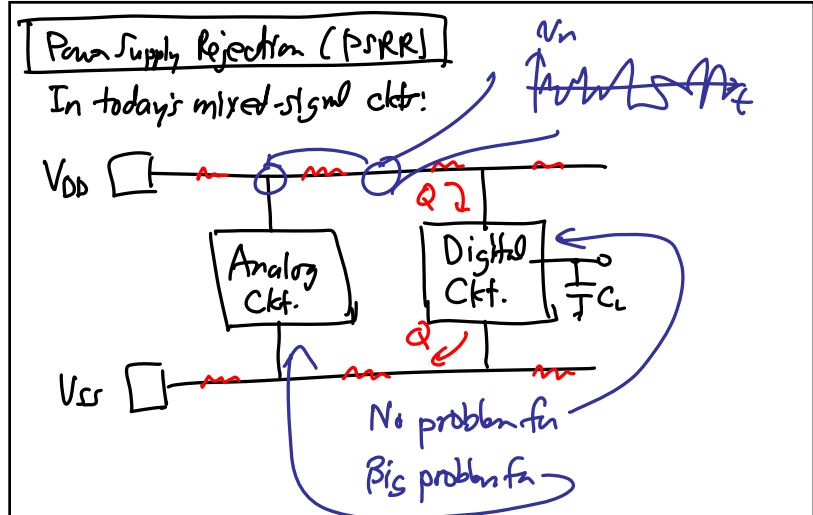


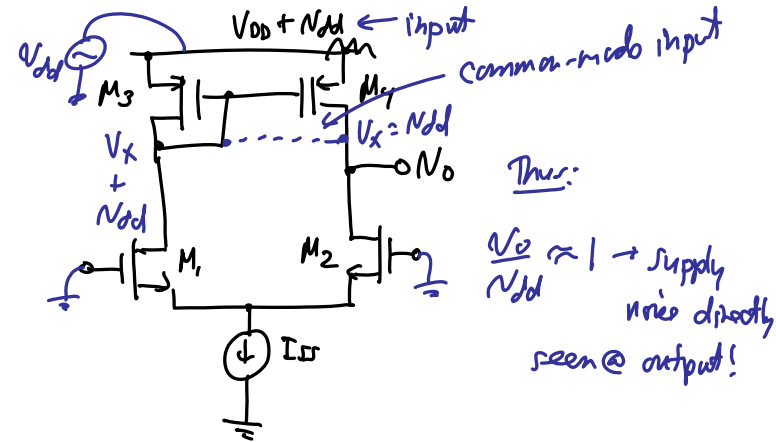
Figure 8.2-3 Response of second-order system with various phase margins.

Obtain Expressions for:

- ①  $V_{overshoot}$
  - ② Settling Time,  $T_s$
- } as functions of phase margin,  $\Phi_m$
- Go through settling time handout



Ex. CMOS Diff. Input Stage w/ Coupled Mirror Load



**Definition: Power Supply Rejection Ratio (PSRR)**

$$PSRR \triangleq \frac{\text{Gain From Input to Output}}{\text{Gain From Supply to Output}} = \frac{A_v |_{N_{dd}=0}}{A_{dd} |_{v_i=0}}$$

Thus, for the above example:

$$PSRR \approx \frac{g_{m2}(r_{o2}||r_{o4})}{1} \Rightarrow PSRR \approx g_{m2}(r_{o2}||r_{o4})$$

For more complicated circuits, much more work is involved.

↳ to make things easier, use a unity gain configuration  
can also get  $PSRR = f(\omega)$